

June 2014

FQA70N15

N-Channel QFET® MOSFET

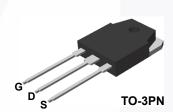
150 V, 70 A, 28 mΩ

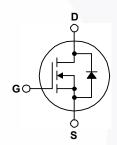
Description

This N-Channel enhancement mode power MOSFET is produced Fairchild using Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched • 175°C Maximum Junction Temperature Rating mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 70 A, 100 V, $R_{DS(on)}$ = 28 m Ω (Max)@ V_{GS} = 10 V, I_D = 35 A
- Low Gate Charge (Typ. 135 nC)
- Low Crss (Typ.135 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA70N15	Unit
V_{DSS}	Drain-Source Voltage		150	V
I _D	Drain Current - Continuous (T _C = 25°	C)	70	Α
	- Continuous (T _C = 100°C)		50	Α
I _{DM}	Drain Curent - Pulsed	(Note 1)	280	А
V_{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ
I _{AR}	Avalanche Current	(Note 1)	70	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	33	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P_{D}	Power Dissipation (T _C = 25°C)		330	W
	- Derate above 25°C		2.2	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQA70N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.45	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA70N15	FQA70N15	TO-3PN	-	-	30

Flectrical Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.15		V/°C
I _{DSS}	7 0 1 1/1 1 1 1 1 1	V _{DS} = 150 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 120 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 35 A		0.023	0.028	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 35 A		48		S
C _{iss}	ic Characteristics Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		4150	5400	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$		840	1100	pF
C _{rss}	Reverse Transfer Capacitance	- 1.0 1911 12		135	175	pF
	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	\\ -75\\ -70 A		60	130	ns
t _r	Turn-On Rise Time	$V_{DD} = 75 \text{ V}, I_{D} = 70 \text{ A},$ $R_{G} = 25 \Omega$		420	850	ns
t _{d(off)}	Turn-Off Delay Time	11G - 20 32		340	690	ns
t _f	Turn-Off Fall Time	(Note 4)		290	590	ns
Qg	Total Gate Charge	V _{DS} = 120 V, I _D = 70 A,	/	135	175	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V		25		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		65		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				70	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				280	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 70 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 70 A,		150	/	ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/μs		0.67		μС

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.34mH, I_{AS} = 70A, V_{DD} = 25V, R_{C} = 25 Ω , Starting T_{J} = 25°C 3. I_{SD} ≤ 70A, di/dt ≤ 300A/ μ s, V_{DD} = BV $_{DSS}$, Starting T_{J} = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

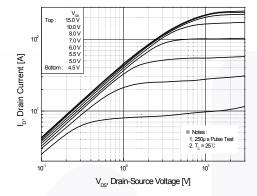


Figure 1. On-Region Characteristics

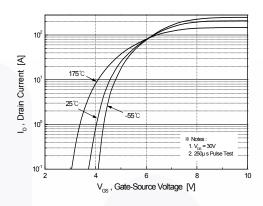


Figure 2. Transfer Characteristics

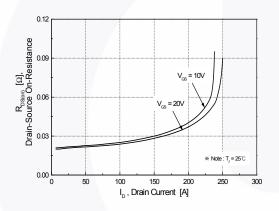


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

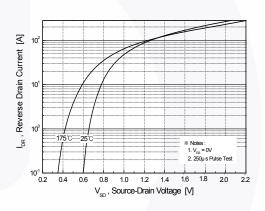


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

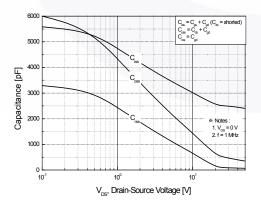


Figure 5. Capacitance Characteristics

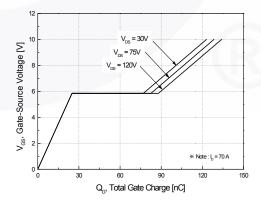


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

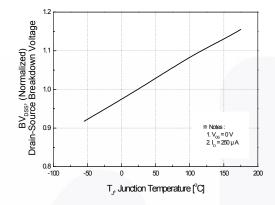


Figure 7. Breakdown Voltage Variation vs. Temperature

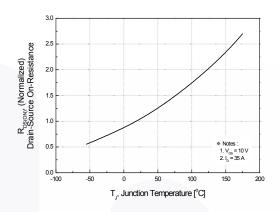


Figure 8. On-Resistance Variation vs. Temperature

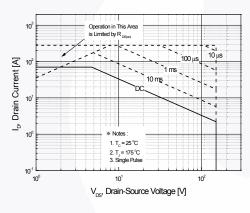


Figure 9. Maximum Safe Operating Area

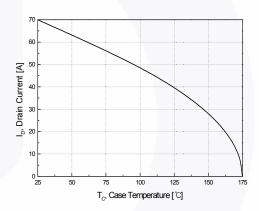


Figure 10. Maximum Drain Current vs. Case Temperature

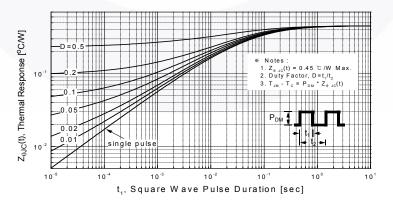


Figure 11. Transient Thermal Response Curve



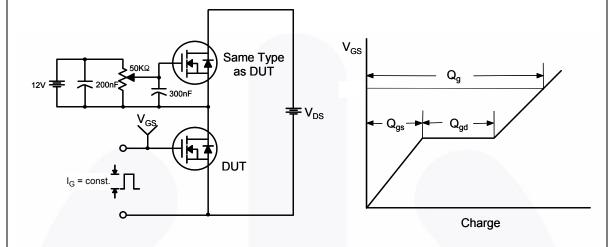


Figure 13. Resistive Switching Test Circuit & Waveforms

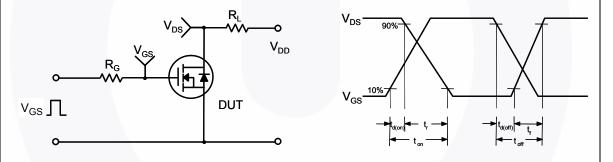
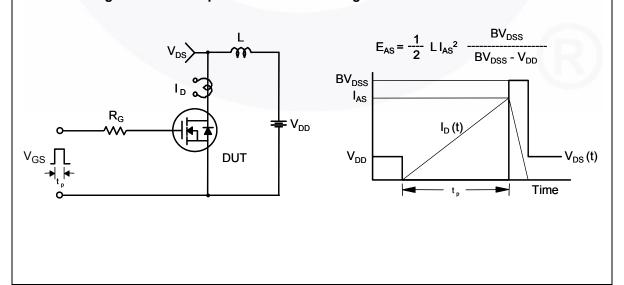
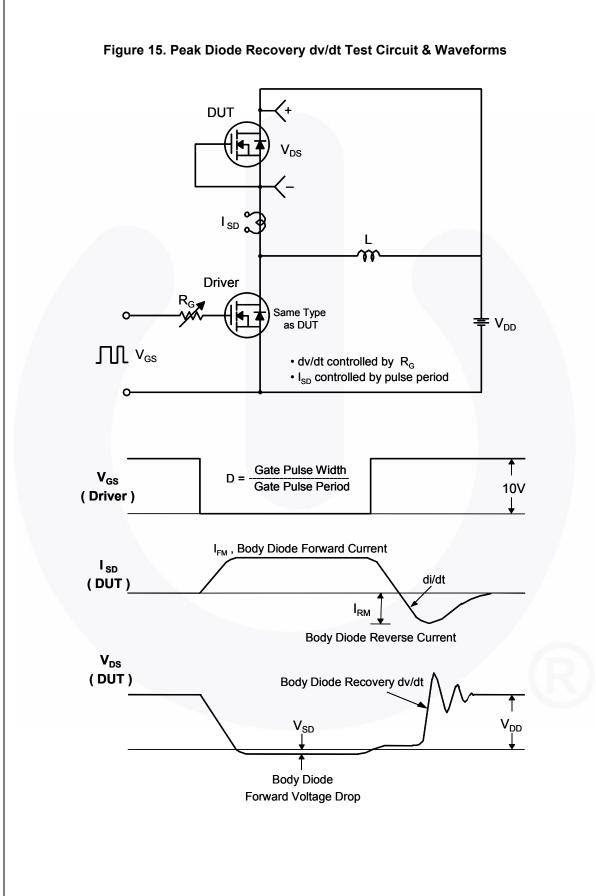


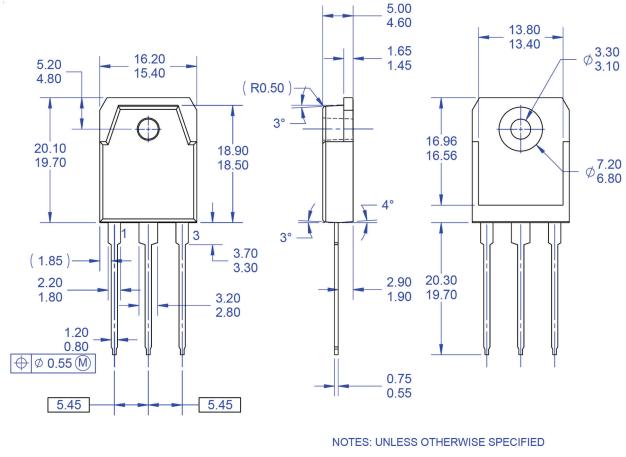
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

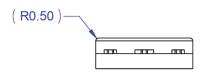




©2000 Fairchild Semiconductor Corporation FQA70N15 Rev. C2

Mechanical Dimensions





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
 DIMENSION AND TOLERANCING PER
- ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAP BitSiC™ Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT™ CTL™ Current Transfer Logic™

DEUXPEED® Dual Cool™ EcoSPARK® EfficentMax™ ESBC™

Fairchild®

Fairchild Semiconductor® FACT Quiet Series™

FACT® FAST® FastvCore™ FETBench™ FPS™

F-PFS™ FRFET®

Global Power ResourceSM GreenBridge™ Green FPS™ Green FPS™ e-Series™

Gmax™ GTO™ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™

MillerDrive™ MotionMax™ mWSaver® OptoHiT™ OPTOLOGIC® OPTOPLANAR® PowerTrench® PowerXS™

Programmable Active Droop™

QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™ Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™

Svnc-Lock™

TRUECURRENT®* uSerDes™ UHC[®] Ultra FRFET™ UniFET™ VCX™ VisualMax™

SYSTEM ®*

TinyBoost®

TinyBuck®

TinyCalc™

TinyLogic[®]

TINYOPTO™

TinvPower™

TinyPWM™

TinyWire™

TranSiC™

TriFault Detect™

VoltagePlus™ XS™ 仙童 ™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, falled application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification Product Status		Definition		
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specification may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























Website:

Welcome to visit www.ameya360.com

Contact Us:

> Address:

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

> Sales:

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com